FAIRCHILD SEMICONDUCTOR®

January 2008

FGA15N120FTD
1200V, 15A Field Stop Trench IGBT

Features

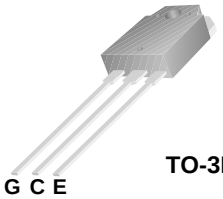
- Field stop trench technology
- High speed switching
- Low saturation voltage: $V_{CE(sat)}$ =1.58V @ I_C = 15A
- High input impedance
- RoHS complaint

Applications

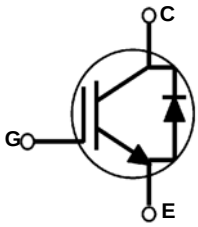
- Induction heating and Microwave oven
- Soft switching applications

General Description

Using advanced field stop trench technology, Fairchild's 1200V trench IGBTs offer superior conduction and switching performances, and easy parallel operation with exceptional avalanche ruggeness. This device is designed for soft switching applications.



TO-3PN



Absolute Maximum Ratings

Symbol	Description		Ratings	Units
V_{CES}	Collector to Emitter Voltage		1200	V
V_{GES}	Gate to Emitter Voltage		± 25	V
I_C	Collector Current	@ T_C = 25°C	30	A
	Collector Current	@ T_C = 100°C	15	A
$I_{CM\ (1)}$	Pulsed Collector Current		45	A
I_F	Diode Continuous Forward Current	@ T_C = 100°C	15	A
I_{FM}	Diode Maximum Forward Current		90	A
P_D	Maximum Power Dissipation	@ T_C = 25°C	220	W
	Maximum Power Dissipation	@ T_C = 100°C	88	W
T_J	Operating Junction Temperature		-55 to +150	°C
T_{stg}	Storage Temperature Range		-55 to +150	°C
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

Notes:
1: Repetitive rating: Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$(IGBT)	Thermal Resistance, Junction to Case	-	0.57	°C/W
$R_{\theta JC}$(Diode)	Thermal Resistance, Junction to Case	-	2.1	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	62.5	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FGA15N120FTD	FGA15N120FTDTU	TO-3PN	-	-	30

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{CES}	Collector to Emitter Breakdown Voltage	V_{GE} = 0V, I_C = 1mA	1200	-	-	V
I_{CES}	Collector Cut-Off Current	V_{CE} = V_{CES}, V_{GE} = 0V	-	-	1	mA
I_{GES}	G-E Leakage Current	V_{GE} = V_{GES}, V_{CE} = 0V	-	-	±250	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	I_C = 15mA, V_{CE} = V_{GE}	3.5	6	7.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C = 15A, V_{GE} = 15V	-	1.58	2	V
		I_C = 15A, V_{GE} = 15V, T_C = 125°C	-	1.83	-	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	V_{CE} = 30V, V_{GE} = 0V, f = 1MHz	-	2350	-	pF
C_{oes}	Output Capacitance		-	70	-	pF
C_{res}	Reverse Transfer Capacitance		-	45	-	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 600V, I_C = 15A, R_G = 15Ω, V_{GE} = 15V, Resistive Load, T_C = 25°C	-	33	-	ns
t_r	Rise Time		-	80	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	160	-	ns
t_f	Fall Time		-	255	330	ns
E_{on}	Turn-On Switching Loss		-	0.3	-	mJ
E_{off}	Turn-Off Switching Loss		-	0.58	0.74	mJ
E_{ts}	Total Switching Loss		-	0.88	-	mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 600V, I_C = 15A, R_G = 15Ω, V_{GE} = 15V, Resistive Load, T_C = 125°C	-	30	-	ns
t_r	Rise Time		-	115	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	170	-	ns
t_f	Fall Time		-	390	-	ns
E_{on}	Turn-On Switching Loss		-	0.38	-	mJ
E_{off}	Turn-Off Switching Loss		-	0.89	-	mJ
E_{ts}	Total Switching Loss		-	1.27	-	mJ
Q_g	Total Gate Charge	V_{CE} = 600V, I_C = 15A, V_{GE} = 15V	-	100	-	nC
Q_{ge}	Gate to Emitter Charge		-	19	-	nC
Q_{gc}	Gate to Collector Charge		-	45	-	nC

Electrical Characteristics of the Diode T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Typ.	Max	Units
V_{FM}	Diode Forward Voltage	I_F = 15A	T_C = 25°C	-	1.4	1.8	V
			T_C = 125°C	-	1.42	-	
t_{rr}	Diode Reverse Recovery Time	I_{ES} =15A, dI/dt = 200A/μs	T_C = 25°C	-	575	-	ns
			T_C = 125°C	-	577	-	
I_{rr}	Diode Peak Reverse Recovery Cyrrent		T_C = 25°C	-	30	-	A
			T_C = 125°C	-	37	-	
Q_{rr}	Diode Reverse Recovery Charge		T_C = 25°C	-	8.7	-	μC
			T_C = 125°C	-	10.7	-	

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

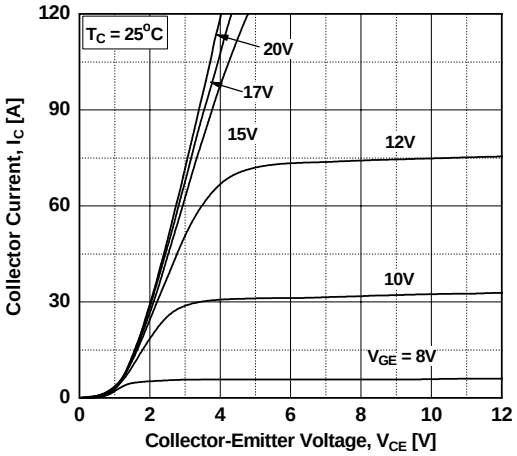


Figure 2. Typical Output Characteristics

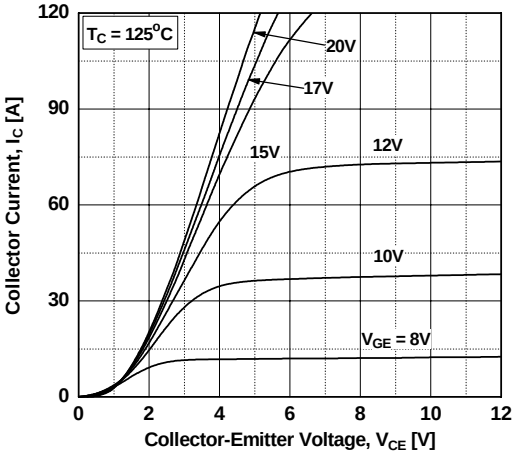


Figure 3. Typical Saturation Voltage Characteristics

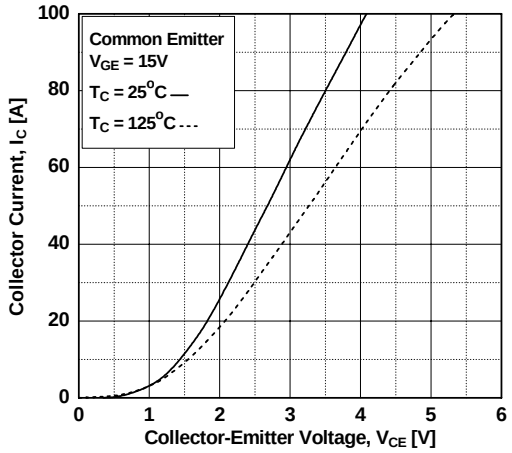


Figure 4. Transfer Characteristics

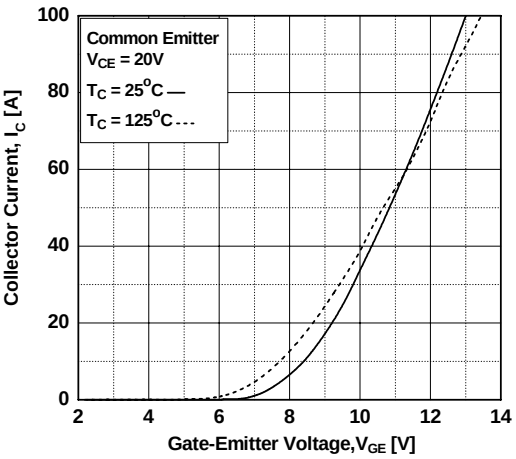


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

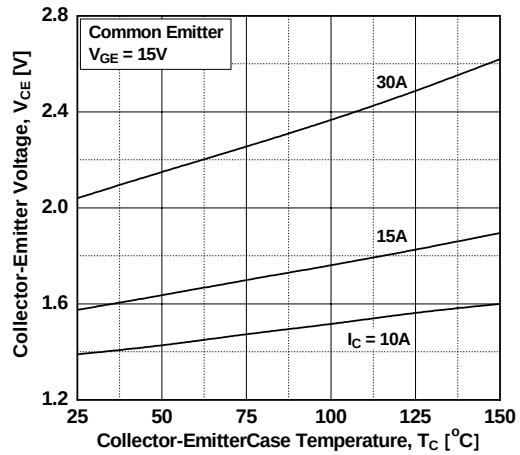
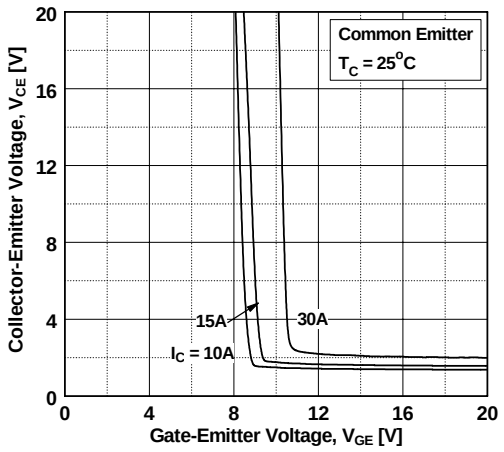


Figure 6. Saturation Voltage vs. V_{GE}



Typical Performance Characteristics

Figure 7. Saturation Voltage vs. V_{GE}

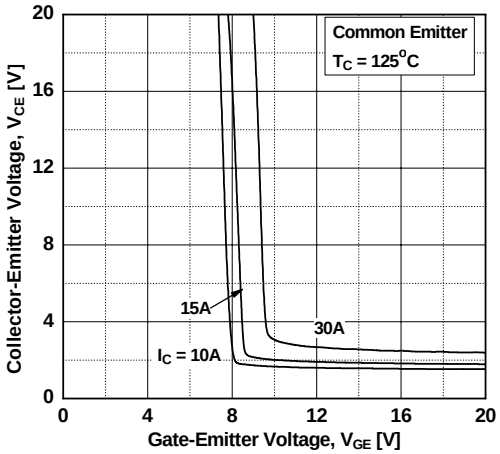


Figure 8. Capacitance Characteristics

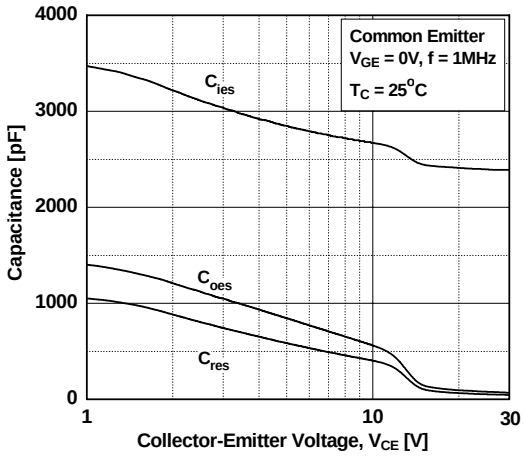


Figure 9. Gate charge Characteristics

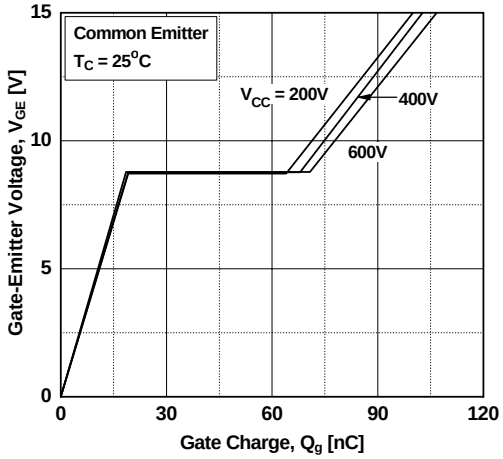


Figure 10. SOA Characteristics

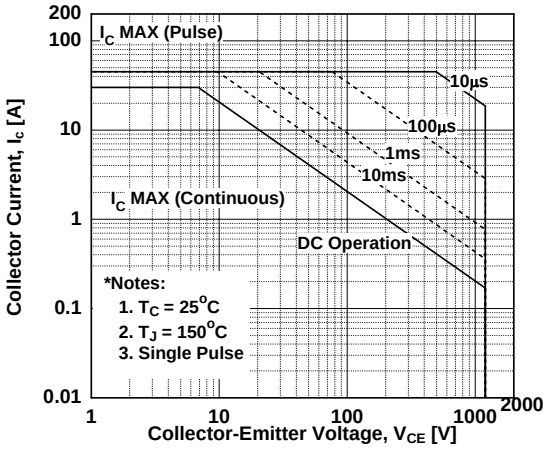


Figure 11. Turn-on Characteristics vs. Gate Resistance

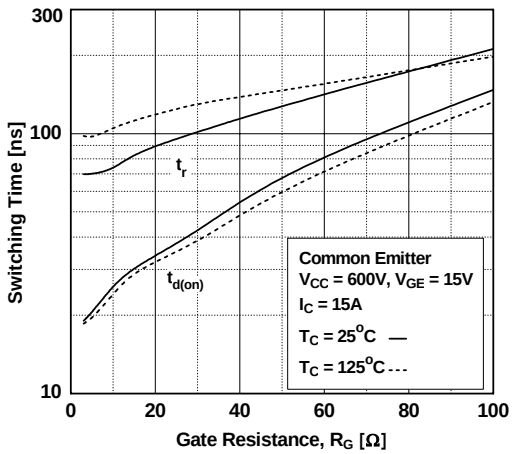
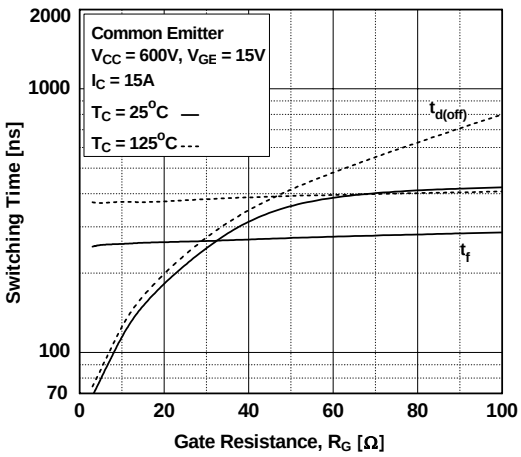


Figure 12. Turn-off Characteristics vs. Gate Resistance



Typical Performance Characteristics

Figure 13. Turn-on Characteristics vs. Collector Current

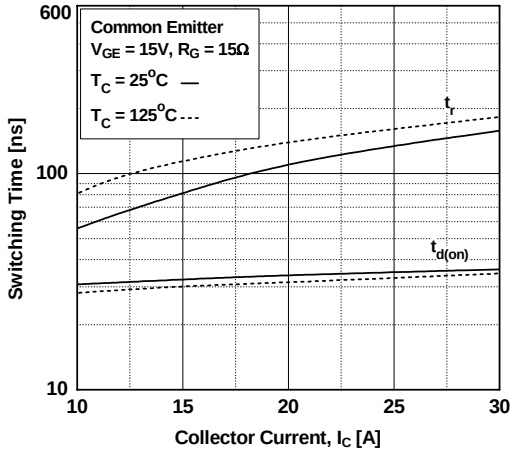


Figure 14. Turn-off Characteristics vs. Collector Current

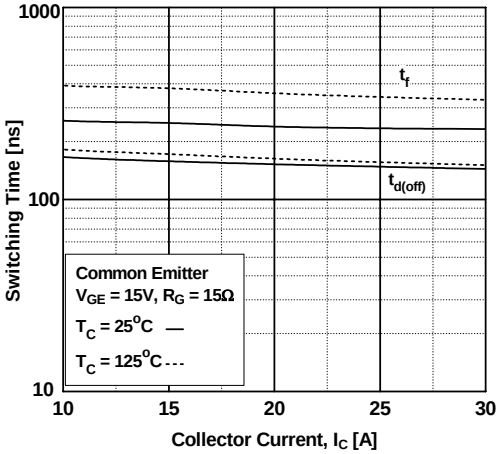


Figure 15. Switching Loss vs. Gate Resistance

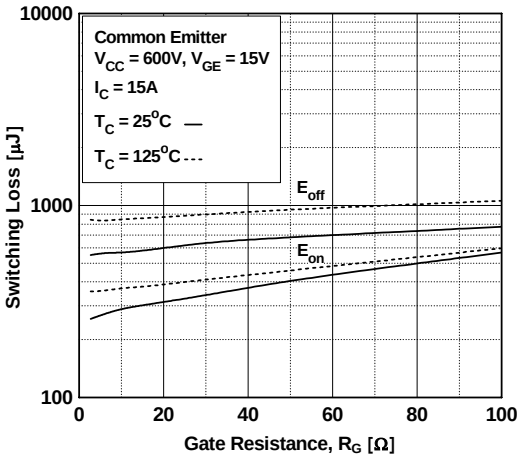


Figure 16. Switching Loss vs. Collector Current

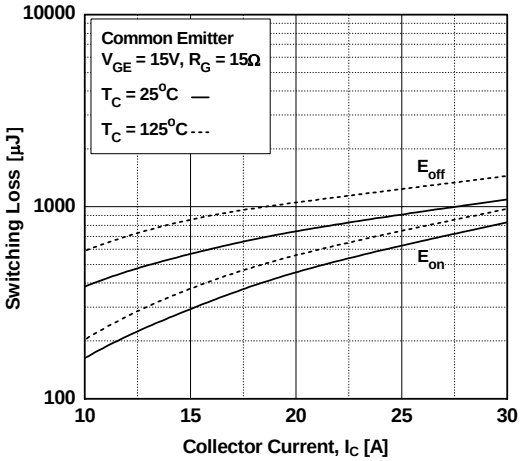


Figure 17. Turn off Switching SOA Characteristics

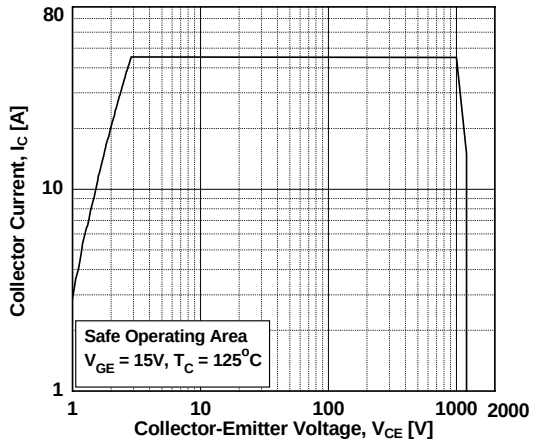
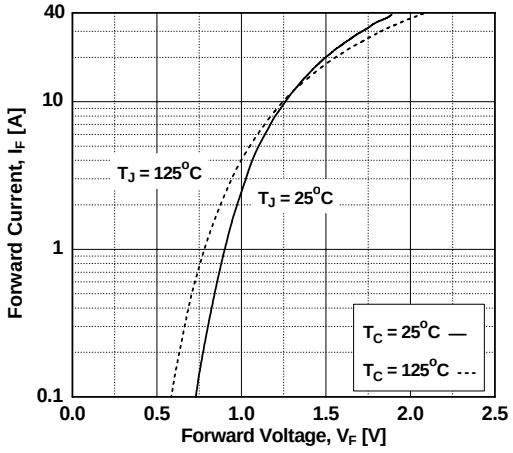


Figure 18. Forward Characteristics



Typical Performance Characteristics

Figure 19. Reverse Recovery Current

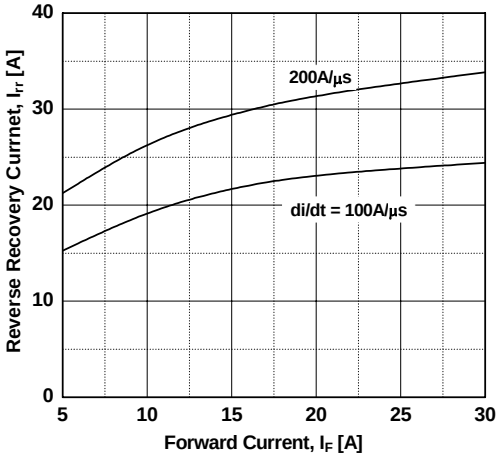


Figure 20. Stored Charge

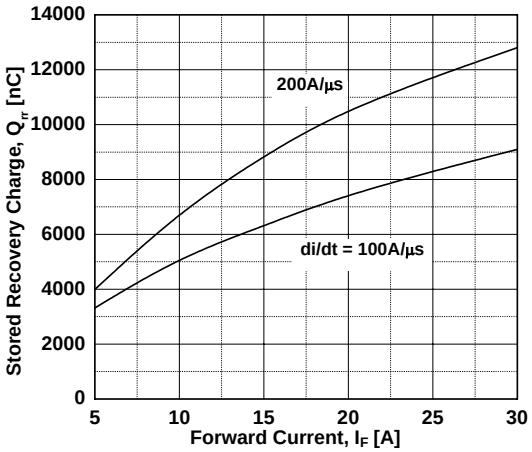


Figure 21.Reverse Recovery Time

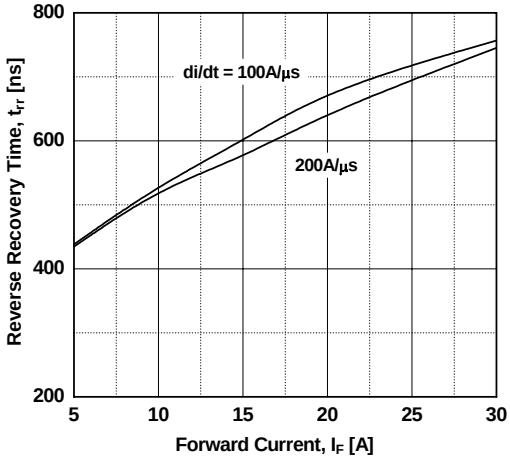
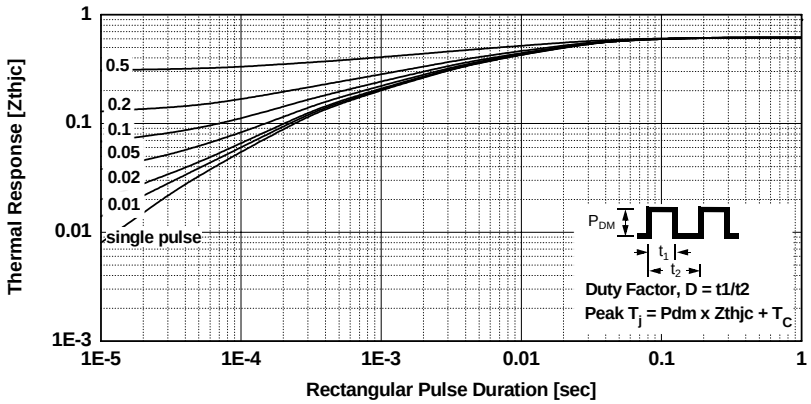
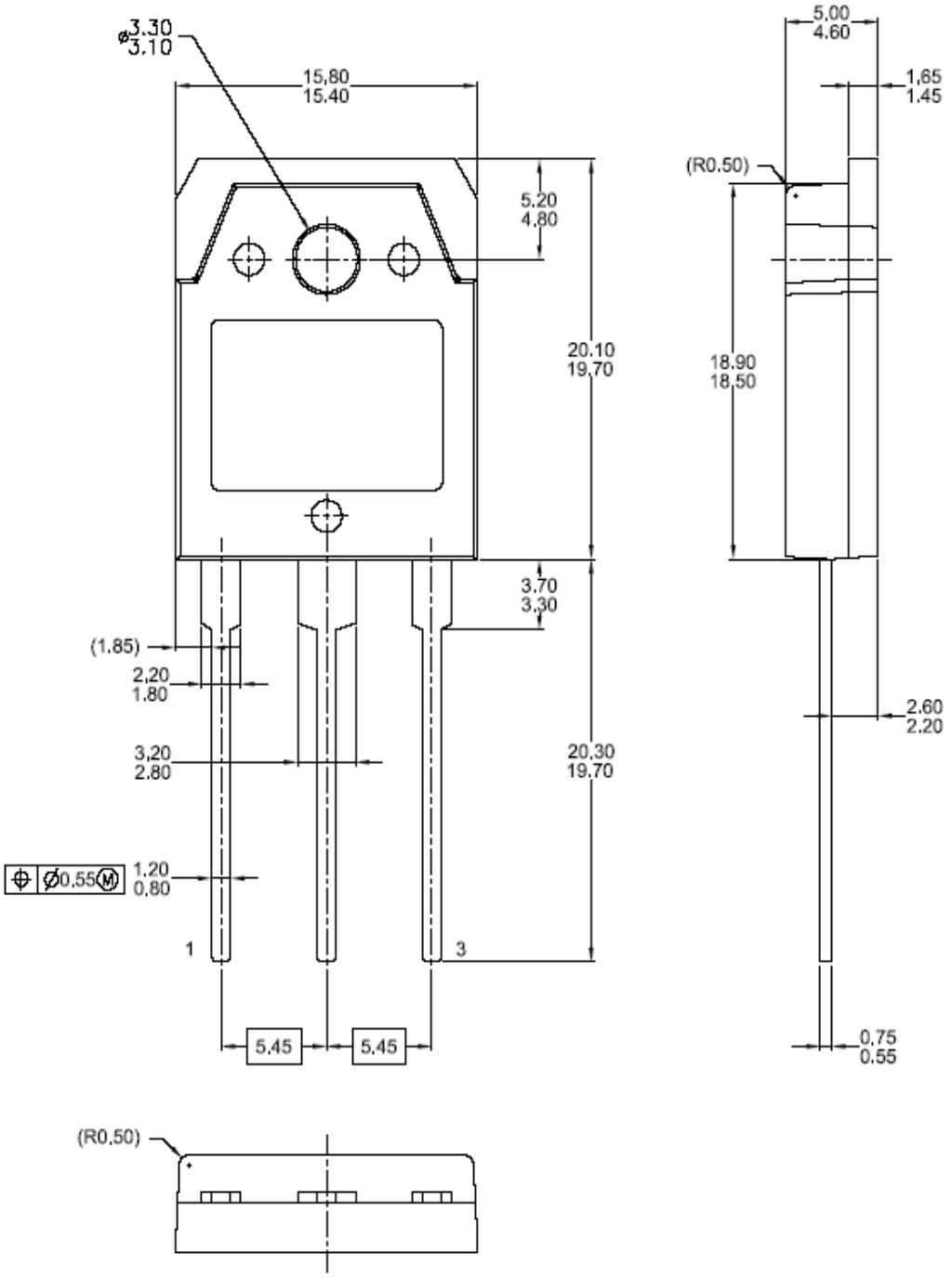


Figure 22.Transient Thermal Impedance of IGBT



Mechanical Dimensions

TO-3PN



Dimensions in Millimeters

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